NSN 5961-01-035-8599

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Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-035-8599 **Inclosure Material:** Metal **Overall Length:** Between 0.874 inches and 1.030 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** Between 1.049 inches and 1.062 inches **Thread Size:** 0.250 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 600.0 repetitive peak reverse voltage and 800.0 nonrepetitive peak reverse voltage and 600.0 repetitive peak off-state voltage **Current Rating Per Characteristic:** 110.00 amperes forward current, total rms nanoamperes **Power Rating Per Characteristic:** 400.0 watts small-signal input power, common-collector blank **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius junction **Special Features:** Junction pattern arrangement: pnpn **Thread Series Designator:** Unf **Terminal Type And Quantity:** 1 threaded stud and 2 tab, solder lug Shelf Life: N/a **Unit Of Measure: Demilitarization:** No